

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A semiconductor device, comprising:
a semiconductor film;
a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film, the gate electrode not covering any end of the semiconductor film.
2. (Previously Presented) A semiconductor device, comprising:
a semiconductor film having a source region and a drain region;
a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film, a width of the gate electrode being smaller than a width of the semiconductor film.
3. (Previously Presented) The semiconductor device according to Claim 1, further comprising a sub gate electrode connected to the gate electrode.
4. (Previously Presented) The semiconductor device according to Claim 3, the sub gate electrode being disposed on the gate electrode.
5. (Previously Presented) The semiconductor device according to Claim 3, the sub gate electrode being disposed so as to cover at least one end of the semiconductor film.
- 6-8. (Canceled).
9. (Previously Presented) A semiconductor device, comprising:
a semiconductor film having a plurality of source regions and drain regions, the semiconductor film including a plurality of regions formed of an intrinsic semiconductor which is not doped with dopant;

a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film;
the regions extending toward at least one of the plurality of source regions and drain regions from the gate electrode and separating adjacent source regions and adjacent drain regions.

10. (Previously Presented) The semiconductor device according to Claim 1,
the semiconductor film being formed on an insulating layer.

11. (Currently Amended) ~~A circuit board, comprising~~A circuit board including a semiconductor device, the semiconductor device comprising:
a semiconductor film; the semiconductor device according to Claim 1; and
a gate insulating film formed on at least part of the semiconductor film;
a gate electrode formed on the gate insulating film, the gate electrode not covering any end of the semiconductor film, a width of the gate electrode being smaller than a width of the semiconductor film; and

wires that supply at least one of signals and electric power to the semiconductor device.

12. (Currently Amended) ~~An electro-optical device, comprising~~An electro-optical device including a circuit board having a semiconductor device, the semiconductor device comprising:

the circuit board according to Claim 11; a semiconductor film;
a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film, the gate electrode not covering any end of the semiconductor film, a width of the gate electrode being smaller than a width of the semiconductor film, the circuit board including a first electrode formed above the circuit board; and

an electro-optical element formed above the first electrode.

13. (Currently Amended) An electro-optical device, comprising:

an electro-optical element; ~~and~~ and a semi-conductor device, the

semiconductor device comprising:

a semiconductor film;

a gate insulating film formed on at least part of the semiconductor film; and

a gate electrode formed on the gate insulating film, the gate electrode not covering any end of the semiconductor film,

a width of the gate electrode being smaller than a width of the semiconductor film;

~~the semiconductor device according to Claim 1,~~ the electro-optical element and the semiconductor device being used as at least one electronic circuit selected from the group consisting of shift registers, level shifters, buffer circuits, and analog switches.

14. (Previously Presented) The electro-optical device according to Claim 12, the electro-optical element being an organic electroluminescence element.

15. (Canceled).

16. (New) A circuit board including a semiconductor device, the semiconductor device comprising:

a semiconductor film;

a gate insulating film formed on at least part of the semiconductor film; and

a gate electrode formed on the gate insulating film, the gate electrode not covering any end of the semiconductor film, a width of the gate electrode being smaller than a width of the semiconductor film.

17. (New) A semiconductor device comprising:

a semiconductor film having a source region and a drain region;

a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film, a width of the gate
electrode being smaller than a width of the semiconductor film in the direction perpendicular
to the source/drain direction.